

PRODUCT/PROCESS CHANGE NOTIFICATION

PCN IPG-DIS/14/8736 Dated 16 Oct 2014

Qualification of a second electrical wafer sort source for SiC diodes

Table 1. Change Implementation Schedule

| Forecasted implementation date for change | 09-Oct-2014 |
|---|-------------|
| Forecasted availability date of samples for customer | 09-Oct-2014 |
| Forecasted date for STMicroelectronics change Qualification Plan results availability | 09-Oct-2014 |
| Estimated date of changed product first shipment | 15-Jan-2015 |

Table 2. Change Identification

| Product Identification (Product Family/Commercial Product) | SiC diodes |
|---|---|
| Type of change | Testing additional location |
| Reason for change | to increase our manufacturing capacity |
| Description of the change | Today ST inhouse plant located in Catania is qualified as EWS (Electrical Wafer Sorting) site for SiC Power schottky diode (STPSC). In Q4 2014, both ST Catania plant and ST Toa Payoh plant will be qualified as EWS site for all SiC Power schottky diode (STPSC) |
| Change Product Identification | internal codification and QA number |
| Manufacturing Location(s) | |

Table 3. List of Attachments

| Customer Part numbers list | |
|----------------------------|--|
| Qualification Plan results | |

| Customer Acknowledgement of Receipt | PCN IPG-DIS/14/8736 |
|---|---------------------|
| Please sign and return to STMicroelectronics Sales Office | Dated 16 Oct 2014 |
| Qualification Plan Denied | Name: |
| Qualification Plan Approved | Title: |
| | Company: |
| Change Denied | Date: |
| Change Approved | Signature: |
| Remark | |
| | |
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| | |

| Name | Function | |
|---------------------|-------------------|--|
| Paris, Eric | Marketing Manager | |
| Duclos, Franck | Product Manager | |
| Rebrasse, Jean-Paul | Q.A. Manager | |

DOCUMENT APPROVAL



(1) IPG: Industrial & Power Group - ASD: Application Specific Device – IPAD™: Integrated Passive and Active Devices

PCN Product/Process Change Notification

| Notification number: | IPG-DIS/14/8736 | Issue Date | 09/10/2014 |
|-------------------------|-----------------|---|-----------------|
| ssued by | Aline AUGIS | | |
| Product series affected | by the change | STPSC1006D STPSC1006G-TR STPSC10H065D STPSC10H065D STPSC10H065D STPSC10H065DY STPSC10H065DY STPSC12H065DY STPSC12H065CT STPSC12H065CT STPSC20H065CT STPSC20H065CT STPSC20H065CTY STPSC20H065CW STPSC20H065CW STPSC20H065CW STPSC40065CW STPSC40065CW STPSC40065DI STPSC40065DI STPSC4H065DI STPSC6H065D STPSC8H065D STPSC8H065CT STPSC8H065D STPSC8H065D STPSC8H065D | |
| be of change : | | Additional electrical wa | fer sort source |

Today ST inhouse plant located in Catania is qualified as EWS (Electrical Wafer Sorting) site for SiC Power schottky diode (STPSC).

In Q4 2014, both ST Catania plant and ST Toa Payoh plant will be qualified as EWS site for all SiC Power schottky diode (STPSC)

STMicroelectronics IPG - ASD & IPAD™ Division¹ BU Rectifiers



(1) IPG: Industrial & Power Group - ASD: Application Specific Device – IPAD™: Integrated Passive and Active Devices

Reason for change

This additional EWS site will increase our manufacturing capacity for a better service on the considered Power Rectifier devices.

| The changed products do not present modified electrical, dimensional or thermal parameters, leaving unchanged the current information published in the product datasheet |
|--|
| The Moisture Sensitivity Level of the part (according to the IPC/JEDEC JSTD-020D standard) remains unchanged. |
| The footprint recommended by ST remains the same. |
| There is no change in the packing modes and the standard delivery quantities either. |
| The products remain in full compliance with the ST ECOPACK®2 grade ("halogen-free"). |
| |

Disposition of former products

Non applicable

Marking and traceability

There is no change on the marking. The traceability is secured by an internal codification and the QA number.

| Qualification complete date | Week 39-2014 |
|-----------------------------|--------------|
| | |

Forecasted sample availability

| Product family | Sub-family | Commercial part Number | Availability date |
|----------------|------------------|---------------------------|-------------------|
| Rectifiers | STPSC serie 600V | STPSCx06xx | W48-2014 |
| Rectifiers | STPSC serie 650V | STPSCxH065xx | W01-2015 |

Change implementation schedule

| Sales types | Estimated production start | Estimated first shipments | |
|---------------------|----------------------------|---------------------------|--|
| STPSC series | W44-2014 | W03-2015 | |
| Comments: | | | |
| Customer's feedback | | | |

Please contact your local ST sales representative or quality contact for requests concerning this change notification.

Absence of acknowledgement of this PCN within 30 days of receipt will constitute acceptance of the change Absence of additional response within 90 days of receipt of this PCN will constitute acceptance of the change



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IPG Group ASD & IPAD division Quality and Reliability

Qualification Report

EWS capacity extension in Singapore – Power Schottky Silicon Carbide diodes

| Gener | al Information | | Locations |
|-------------------------------------|--------------------------------------|----------------|---------------------|
| Product Line Product Description | Rectifiers Silicon Carbide diodes | Wafer fab | ST Catania (ITALY) |
| Product Group | IPG | EWS plat | ST Singapore |
| Product division Package | ASD & IPAD Multiple | Assembly plant | ST Shenzhen (CHINA, |
| Maturity level step | Qualified | Assessment | PASS |

DOCUMENT INFORMATION

| Version | Date | Pages | Prepared by | Approved by | Comment |
|---------|------------|-------|-------------|-------------|---------|
| Rev 1 | 10/09/2014 | 5 | A. Dromel | JP Rebrasse | |

Note: This report is a summary of the test trials performed in good faith by STMicroelectronics in order to evaluate the potential risks during the product life using a set of defined test methods.

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<u>1</u> APPLICABLE AND REFERENCE DOCUMENTS

| Document reference | Short description | | |
|--------------------|--|--|--|
| JESD47-H | Stress-Test-Driven Qualification of Integrated Circuits | | |
| AEC Q101 | Stress test qualification for automotive grade discrete semiconductors | | |

2 GLOSSARY

| SS | Sample Size | | | |
|-----|--------------------------|--|--|--|
| EWS | Electrical Wafer Sorting | | | |
| ТРҮ | Toa Payoh | | | |
| АМК | Ang Mo Kio | | | |

3 EVALUATION OVERVIEW

3.1 Objectives

The objective of this report is to confirm that the new EWS test location in Toa Payoh has no impact on products and production flow.

The involved products are listed in the table below:

| Product sub-Family | | Product devices |
|---|---|--|
| Silicon Carbide Power Schottky Rectifiers | STPSC1006D STPSC1006G-TR STPSC10H065B-TR STPSC10H065D STPSC10H065DI STPSC10H065DY STPSC10H065G-TR STPSC10H065G-TR STPSC1206D STPSC12C065D-L STPSC12H065CT STPSC12H065CT STPSC20H065CT STPSC20H065CTY STPSC20H065CTY STPSC20H065CW STPSC20H065CW STPSC20H065CW STPSC20H065CW STPSC40065CW | STPSC406D STPSC4H065B-TR STPSC4H065D STPSC4H065DI STPSC606D STPSC606G-TR STPSC606G-TR STPSC6H065B-TR STPSC6H065DI STPSC6H065DI STPSC6H065G-TR STPSC6H12B-TR1 STPSC6H12B-TR1 STPSC6H12B-TR1 STPSC806D STPSC806D STPSC806G-TR STPSC8H065B-TR STPSC8H065D-TR STPSC8H065D STPSC8H065DI STPSC8H065DI STPSC8H065DI STPSC8H065C-TR STPSC8H065C-TR STPSC8H065C-TR STPSC8H065C-TR STPSC8H065C-TR STPSC8H065C-TR |

3.2 Conclusion

The flow study and comparative tests have shown that the devices will be tested exactly with same conditions with no impact on final electrical results.



4 CHANGE DESCRIPTION

The EWS testing flow remains identical in the new site, involving same equipment except inking prober as indicated in the table below. There is consequently no impact on the electrical parameters.

| Description | Current | New | |
|------------------|--|--|--|
| Wafer Fab | Italy Catania | Italy Catania | |
| EWS Area | Italy Catania | Singapore Toa Payoh | |
| EWS process flow | Test – SBL– Inking – QA Gate | Test – SBL– Inking – QA Gate | |
| Tester | SPEA Tester (C430MX) + TEL P8 Prober | SPEA Tester (C430MX) + TEL P8 Prober | |
| Test programs | SPEA test pgms using SPEA test function library (Multi-site) | SPEA test pgms using SPEA test function library (Multi-site) | |
| Inking Prober | TEL P8XL | EG2001 | |
| Assembly and FT | Same flow | Same flow | |



5 TESTS RESULTS SUMMARY

5.1 Test vehicle

| Lot # | Die code | Lot number | Wafer numbers |
|-------|----------|------------|-----------------|
| Lot1 | MDC071Y4 | Y342892 | Wafer 01 |
| Lot2 | MDC071Y4 | Y404986 | Wafers 01 to 11 |
| Lot3 | MDC071Y4 | Y404984 | Wafers 01 & 02 |

5.2 Test plan and results summary

| Lot # Wafer # | Mean comparison | СРК | Yields at EWS test in Catania | Yields at EWS test in Toa Pa Yoh | Acceptance criteria: yield ∆ < 1% |
|------------------|--|-----------------------------|----------------------------------|-------------------------------------|--------------------------------------|
| Lot1 | All parameters mean difference <2% | All parameters Cpk >2 | 97.1% | 96.5% | Pass |
| Lot3 wafer 01 | All parameters mean difference <2% | All parameters Cpk >2 | 96.7% | 96.4% | Pass |
| Lot3 wafer 02 | All parameters mean difference <2% | All parameters Cpk >2 | 97.3% | 96.6% | Pass |

| Lot # | EWS flow at Toa Pa Yoh | СРК | Yields at EWS test in Toa Pa Yoh | Result |
|-------|---------------------------|---------------------------------|-------------------------------------|--------|
| Lot2 | Validated | All parameters Cpk >2 (*) | 95.9% | Pass |

(*) Exception Vf@1mA cpk>1.3

All Cpk of comparative measurements for datasheet parameters have revealed to be superior to 2, which warrants the full correlation between the testing results

Comparative yields have also proved to be fully correlated. Pareto defect and wafer maps have been studied carefully and compared. It appears that no major difference has been raised. Final test remains unchanged.

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